

KSP8598/8599

- Amplifier Transistor

 Collector-Emitter Voltage: V_{CEO}= KSP8598: 60V KSP8599: 80V
- Collector Power Dissipation: P_C (max)=625mW
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



1. Emitter 2. Base 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage		
	: KSP8598	-60	V
	: KSP8599	-80	V
V _{CEO}	Collector-Emitter Voltage		
	: KSP8598	-60	V
	: KSP8599	-80	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-500	mA
P _C	Collector Power Dissipation	625	mW
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage : KSP8598 : KSP8599	I _C = -100μA, I _E =0	-60 -80		V
BV _{CEO}	* Collector-Emitter Breakdown Voltage : KSP8598 : KSP8599	I _C = -10mA, I _B =0	-60 -80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = -10μA, I _C =0	-5		V
I _{CBO}	Collector Cut-off Current : KSP8598 : KSP8599	V _{CB} = -60V, I _E =0 V _{CB} = -80V, I _E =0		-100 -100	nA nA
I _{CEO}	Collector Cut-off Current	V _{CE} = -60V, I _B =0		-100	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = -4V, I _C =0		-100	nA
h _{FE}	* DC Current Gain	V _{CE} = -5V, I _C = -1mA V _{CE} = -5V, I _C = -10mA V _{CE} = -5V, I _C = -100mA	100 100 75	300	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = -100mA, I _B = -5mA I _C = -100mA, I _B = -10mA		-0.4 -0.3	V V
V _{BE} (on)	* Base-Emitter On Voltage : KSP8598 : KSP8599	V _{CE} = -5V, I _C = -1mA V _{CE} = -5V, I _C = -10mA	-0.5 -0.6	-0.7 -0.8	V
f _T	Current Gain Bandwidth Product	V _{CE} = -5V, I _C = -10mA f=100MHz	150		MHz
C _{ob}	Output Capacitance	V _{CB} = -5V, I _E =0 f=1MHz		8	pF

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Characteristics

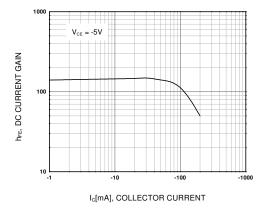


Figure 1. DC current Gain

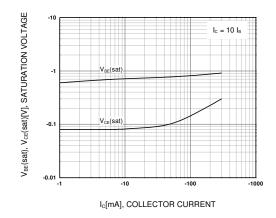


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

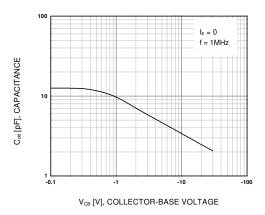


Figure 3. Output Capacitance

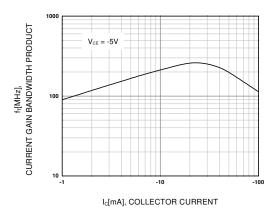
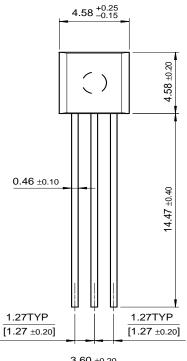
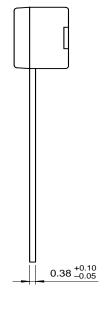
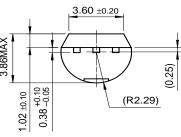


Figure 4. Current Gain Bandwidth Product

TO-92







Dimensions in Millimeters

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